

STD830CP40

Complementary transistor pair in a single package

Features

- Low V_{CE(sat)}
- Simplified circuit design
- Reduced component count
- Low spread of dynamic parameters

Applications

■ Compact fluorescent lamp (CFL) 220 V mains

Description

The STD830CP40 is a hybrid complementary pair of power bipolar transistors manufactured by using the high voltage multi-epitaxial planar technology for high switching speeds and medium voltage capability.

The STD830CP40 is housed in dual island DIP-8 package with separated terminals for higher assembly flexibility, specifically recommended to be used in a new solution for compact fluorescent lamp (CFL).

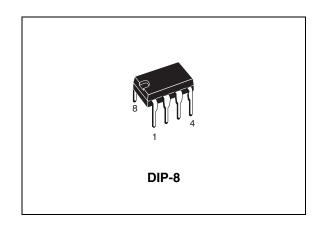


Figure 1. Internal schematic diagram

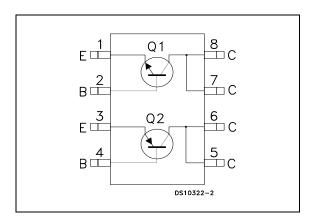


Table 1. Device summary

Order code	Marking	Package	Packing
STD830CP40	D830CP40	DIP-8	Tube

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Electrical ratings STD830CP40

1 Electrical ratings

Table 2. Absolute maximum ratings

Cumbal	Dougneston	Value		I I mit	
Symbol	Parameter	NPN	PNP	Unit	
V_{CBO}	Collector-base voltage (I _E = 0)	700	500	V	
V_{CEO}	Collector-emitter voltage (I _B = 0) 400		00	٧	
V_{EBO}	V_{EBO} Emitter-base voltage ($I_C = 0$, $I_b = 1.5$ A, $t_p < 10$ ms)		V _{(BR)EBO}		
I _C	Collector current		3		
I _{CM}	Collector peak current (t _P < 5ms) 6		3	Α	
Ι _Β	Base current		1.5		
I _{BM}	Base peak current (t _P < 1ms)	3		Α	
P _{tot}	P _{tot} Total dissipation at T _{amb} = 25°C single transistor TBD		3D	W	
P _{tot}	Total dissipation at T _{amb} = 25°C both transistors		TBD		
T _{stg}	Storage temperature	-65 to 150		°C	
T _J	Max. operating junction temperature	150		°C	

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-amb} ⁽¹⁾	Thermal resistance junction-ambient (Single transistor)	TBD	°C/W
R _{thj-amb} ⁽¹⁾	Thermal resistance junction-ambient (Both transistors)	TBD	°C/W

^{1.} When mounted on 1 inch square pad of 2 oz. copper, $t \le 10$ sec.

Note: For PNP types voltage and current values are negative

2 Electrical characteristics

(T_{case} = 25°C unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector cut-off current (V _{BE} = 0)	For NPN: $V_{CE} = 700 \text{ V}$ $V_{CE} = 700 \text{ V}$ $V_{CE} = 700 \text{ V}$ $V_{CE} = 125^{\circ}\text{C}$ For PNP: $V_{CE} = 500 \text{ V}$ $V_{CE} = 500 \text{ V}$ $V_{CE} = 500 \text{ V}$ $V_{CE} = 125^{\circ}\text{C}$			0.1 0.5 0.1 0.5	mA mA mA
V _{(BR)EBO}	Emitter-base breakdown voltage (I _C = 0)	I _E = 10 mA For NPN: For PNP:	10 5		18 10	V V
V _{CEO(sus)} ⁽¹⁾	Collector-emitter sustaining voltage (I _B = 0)	I _C = 5 mA	400			V
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	$I_C = 0.7 \text{ A}$ $I_B = 0.1 \text{ A}$ $I_B = 0.2 \text{ A}$			0.5 0.5	V V
V _{BE(sat)} ⁽¹⁾	Base-emitter saturation voltage	$I_C = 0.5 \text{ A}$ $I_B = 0.1 \text{ A}$ $I_C = 1 \text{ A}$ $I_B = 0.2 \text{ A}$			1.1 1.2	V V
h _{FE} ⁽¹⁾	DC current gain	$I_{C} = 10 \text{ mA}$ $V_{CE} = 5 \text{ N}$ $I_{C} = 0.7 \text{ A}$ $V_{CE} = 5 \text{ N}$ $I_{C} = 2 \text{ A}$ $V_{CE} = 5 \text{ N}$	/ 18		34	
t _r t _s	Resistive load Rise time Storage time Fall time	$I_C = 0.7 \text{ A}$ $V_{CC} = 250 \text{ N}$ $I_{B1} = 0.14 \text{ A}$ $I_{B2} = -0.14 \text{ A}$ $t_p = 30 \mu\text{s}$	A	100 2.4 100		ns µs ns
t _s	Inductive load Storage time Fall time	$\begin{split} I_{C} &= 1 \text{ A} & I_{B1} &= 0.2 \text{ A} \\ V_{BE(off)} &= -5 \text{ V} & R_{BB} &= 0 \\ V_{clamp} &= 200 \text{ V} & L &= 1 \text{ mHz} \end{split}$		450 100		ns ns

^{1.} Pulsed: Pulse duration = 300 μ s, duty cycle \leq 1.5 %

Note: For PNP types voltage and current values are negative

3 Package mechanical data

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Table 5. DIP-8 mechanical data

Di		mm.	
Dim.	Min.	Тур.	Max.
А			4.80
A1	0.50		
A2	3.10		3.50
A3	1.40		1.60
b	0.38		0.55
b1	0.38		0.51
b2	1.47		1.57
b3	0.89		1.09
С	0.21		0.35
c1	0.20		0.30
D	9.10		9.30
D1	0.13		
E	7.62		8.25
E1	6.25		6.45
е		2.54	
eA		7.62	
eB	7.62		10.90
eC	0		1.52
L	2.92		3.81

 e^{c} GAUGE PLANE 0.38 eBвА Ш A3 8145726_A

Figure 2. Drawing dimension DIP-8

Revision history STD830CP40

4 Revision history

Table 6. Document revision history

Date	Revision	Changes
27-May-2009	1	Initial release.

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